L Number	Hits	Search Text	DB	Time stamp
-	5	("by-pass" or (by adj pass)) with	USPAT;	2003/10/05 15:19
		capacitor and ("multi-level" or (multi adj	JPO;	
		level) or "MLM")	DERWENT	
-	24		USPAT;	2003/10/05 15:20
		capacitor and metallization	JPO;	
	426	 (etch\$4 with first with dielectric) same	DERWENT	2002/10/05 15:25
_	420	(deposit\$ with electrode) and (etch\$4 with	USPAT; JPO;	2003/10/05 15:25
		second with dielectric) same (deposit\$	DERWENT	
		with (second or top or upper) with	DBKWBIVI	
		electrode)		-
_	4	((etch\$4 with first with dielectric) same	USPAT;	2003/10/05 15:23
		(deposit\$ with electrode) and (etch\$4 with	JPO;	
		second with dielectric) same (deposit\$	DERWENT	
		with (second or top or upper) with		
		electrode)) and adjust\$4 with thickness		
_	72	with (dielectric or insulator)	HCDAM.	2003/10/05 15:25
_	12	((etch\$4 with first with dielectric) same (deposit\$ with electrode) and (etch\$4 with	USPAT; JPO;	2003/10/03 13:23
		second with dielectric) same (deposit\$	DERWENT	
		with (second or top or upper) with		
		electrode)) and dielectric adj constant		
-	44	(((etch\$4 with first with dielectric) same	USPAT;	2003/10/05 15:26
		(deposit\$ with electrode) and (etch\$4 with	JPO;	
		second with dielectric) same (deposit\$	DERWENT	
		with (second or top or upper) with		
:		electrode)) and dielectric adj constant) and silicon adj nitride		
_	16	1	USPAT;	2003/10/05 15:26
	10	same (deposit\$ with electrode) and (etch\$4	JPO;	2003, 10, 03 13:20
		with second with dielectric) same	DERWENT	
		(deposit\$ with (second or top or upper)		
		with electrode)) and dielectric adj		
		constant) and silicon adj nitride) and		
	106674	angstroms		2002/10/05 15:26
_	106674	"8" and polish\$4	USPAT; JPO;	2003/10/05 15:26
			DERWENT	
_	l 0	(((((etch\$4 with first with dielectric)	USPAT;	2003/10/05 15:27
		same (deposit\$ with electrode) and (etch\$4	JPO;	
		with second with dielectric) same	DERWENT	
		(deposit\$ with (second or top or upper)		
1		with electrode)) and dielectric adj		
		constant) and silicon adj nitride) and		
	13	<pre>angstroms) and polish\$4) and composite (((((etch\$4 with first with dielectric)</pre>	USPAT;	2003/10/05 16:07
_	13	same (deposit\$ with electrode) and (etch\$4	JPO;	2003/10/03 10:07
		with second with dielectric) same	DERWENT	
	1	(deposit\$ with (second or top or upper)		
[with electrode)) and dielectric adj		
		constant) and silicon adj nitride) and		
İ	_	angstroms) and polish\$4		
-	2	"6329666"	USPAT;	2003/10/05 15:28
			JPO;	
_	1	((((((etch\$4 with first with dielectric)	DERWENT USPAT;	2003/10/05 16:09
	1	same (deposit\$ with electrode) and (etch\$4	JPO;	2003/10/03 10:09
	1	with second with dielectric) same	DERWENT	
		(deposit\$ with (second or top or upper)		
		with electrode)) and dielectric adj		
		constant) and silicon adj nitride) and		
		angstroms) and polish\$4) and (multi with		
	1400	level or "MLM")	HCDAM.	2002/10/05 16:00
_	1406	(multi with level or "MLM") same (dielectric or insulator)	USPAT; JPO;	2003/10/05 16:09
		(dielectic of insulator)	DERWENT	
-	264	((multi with level or "MLM")same	USPAT;	2003/10/05 16:10
		(dielectric or insulator)) same etch\$ with	JPO;	
		(dielectric or insulator)	DERWENT	
	l	1 /2-1-100110 01 1110414001/		l

-	13	(((multi with level or "MLM")same	USPAT;	2003/10/05 16:11
		(dielectric or insulator)) same etch\$ with	JPO;	
		(dielectric or insulator)) same deposit\$4 with electrode	DERWENT	
_	9	((((multi with level or "MLM")same	USPAT;	2003/10/05 16:18
		(dielectric or insulator)) same etch\$ with	JPO;	2000, 10, 00 10, 10
		(dielectric or insulator)) same deposit\$4	DERWENT	
		with electrode) and capacitor		
-	149	VLSI and ("by-pass" or by adj pass)	USPAT;	2003/10/05 16:19
			JPO; DERWENT	
_	0	(VLSI and ("by-pass" or by adj pass)) and	USPAT;	2003/10/05 16:20
	_	electrode and MIM	JPO;	
			DERWENT	
-	26	(VLSI and ("by-pass" or by adj pass)) and	USPAT;	2003/10/05 16:21
		electrode	JPO; DERWENT	
_	0	MIM and (by adj pass) and MLM	USPAT;	2003/10/05 16:21
	Ĭ	inin ana (by da) pass, and inin	JPO;	2003/10/03 10.21
			DERWENT	
-	0	, (-,) p,,,,	USPAT;	2003/10/05 16:21
		adj metallization	JPO;	
_	0	 (by adj pass) and multi adj layer adj	DERWENT USPAT;	2003/10/05 16:47
		metallization	JPO;	2003/10/03 10:4/
			DERWENT	
-	5	"6271596"	USPAT;	2003/10/05 17:09
			JPO;	
	18	HMTMU come multi with love with motel	DERWENT	2003/10/05 17:09
-	1.0	"MIM" same multi with layer with metal	USPAT; JPO;	2003/10/05 17:09
		•	DERWENT	
-	19	"MIM" same multi with layer with metal\$7	USPAT;	2003/10/05 17:09
			JPO;	
		(HMTMH come multi-vith loves with matel C7)	DERWENT	2002/10/05 17.00
-	8	("MIM" same multi with layer with metal\$7) and etch\$4 with dielectric	USPAT; JPO;	2003/10/05 17:09
		and etchy with diciectife	DERWENT	
-	8	("MIM" same multi with layer with metal\$7)	USPAT;	2003/10/05 17:10
		and etch\$4 with (dielectric or insulator)	JPO;	
	_	//WATMU	DERWENT	2003/10/05 17:16
-	5	(("MIM" same multi with layer with metal\$7) and etch\$4 with (dielectric or	USPAT; JPO;	2003/10/03 17:16
		insulator)) and electrode	DERWENT	
-	0	MIM same (multi with level) and parallel	USPAT;	2003/10/05 17:17
		with dishing	JPO;	
_	0	metal same (multi with level) and parallel	DERWENT USPAT;	2003/10/05 17:17
-		with dishing	JPO;	2003/10/03 1/:1/
			DERWENT	
-	0	MIM same (multi with level) and dishing	USPAT;	2003/10/05 17:17
			JPO;	
_	10	MIM same (multi with level)	DERWENT USPAT;	2003/10/05 17:18
_	10	min same (multi with level)	JPO;	2003/10/03 17:18
			DERWENT	
-	340	MIM same wiring	USPAT;	2003/10/05 17:18
			JPO;	
	0	(MTM same wiring) and samallal with	DERWENT	2003/10/05 17:18
_		(MIM same wiring) and parallel with dishing	USPAT; JPO;	2003/10/03 1/:18
			DERWENT	
-	0	(MIM same wiring) and parallel and dishing	USPAT;	2003/10/05 17:19
			JPO;	
	0	(MIM come wiring) and dishi	DERWENT	2003/10/05 17:10
-		(MIM same wiring) and dishing	USPAT; JPO;	2003/10/05 17:19
			DERWENT	
-	128645	(MIM same wiring) electrode and etch\$	USPAT;	2003/10/05 17:19
			JPO;	
		<u></u>	DERWENT	

_	142	(MIM same wiring) and electrode and etch\$4	USPAT; JPO;	2003/10/05 17:19
_	116	((MIM same wiring) and electrode and etch\$4) and (wiring with electrode)	DERWENT USPAT; JPO;	2003/10/05 17:19
-	92	(((MIM same wiring) and electrode and etch\$4) and (wiring with electrode)) and	DERWENT USPAT; JPO;	2003/10/05 17:21
-	1	<pre>(insulator or dielectric) ((((MIM same wiring) and electrode and etch\$4) and (wiring with electrode)) and</pre>	DERWENT USPAT; JPO;	2003/10/05 17:20
-	4	<pre>(insulator or dielectric)) and (multi adj layer with metal\$7) ((((MIM same wiring) and electrode and etch\$4) and (wiring with electrode)) and</pre>	DERWENT USPAT; JPO;	2003/10/05 17:20
		(insulator or dielectric)) and (multi with layer with metal\$7)	DERWENT	2002/10/05 17:22
-	0	<pre>((((MIM same wiring) and electrode and etch\$4) and (wiring with electrode)) and (insulator or dielectric)) and "MLMD"</pre>	USPAT; JPO; DERWENT	2003/10/05 17:22
-	0	(multi with layer with metallization with device) and MIM	USPAT; JPO;	2003/10/05 17:22
_	1	(multi with layer with metallization with device) and metal with capacitor	DERWENT USPAT; JPO;	2003/10/05 17:22
-	124	multi with layer with metallization with device	DERWENT USPAT; JPO;	2003/10/05 17:37
	_		DERWENT	
-	3	("5591677" "6093637" "6239026").PN. (("5591677" "6093637" "6239026").PN.) and capacitor	USPAT; USPAT; JPO;	2003/10/05 17:36 2003/10/05 17:36
_	3	multi with layer with metallization and	DERWENT USPAT; JPO;	2003/10/05 17:38
_	157	metallization and MIM	DERWENT USPAT; JPO;	2003/10/05 17:40
-	89	metallization with layer and MIM	DERWENT USPAT; JPO;	2003/10/05 17:40
_	30	(metallization with layer and MIM) and etch\$4 with dielectric	DERWENT USPAT; JPO;	2003/10/05 17:40
_	23	((metallization with layer and MIM) and etch\$4 with dielectric) and electrode	DERWENT USPAT; JPO;	2003/10/05 17:42
-	20	etch\$4 with dielectric) and electrode) and	DERWENT USPAT; JPO;	2003/10/05 17:43
	36	(lines or wiring) "multi-layer" adj metallization and capacitor	DERWENT USPAT; JPO;	2003/10/05 17:51
_	9	("multi-layer" adj metallization and capacitor) and etch\$4 with dielectric	DERWENT USPAT; JPO;	2003/10/05 17:48
-	507	((lower or bottom or first) adj electrode) same signal adj lines	DERWENT USPAT; JPO;	2003/10/05 17:51
-	84	(((lower or bottom or first) adj electrode) same signal adj lines) same	DERWENT USPAT; JPO;	2003/10/05 17:49
-	0	<pre>parallel (((((lower or bottom or first) adj electrode) same signal adj lines) same parallel) and (insulator or dielectric))</pre>	DERWENT USPAT; JPO; DERWENT	2003/10/05 17:49
_	0	and "high-k" (((((lower or bottom or first) adj electrode) same signal adj lines) same	USPAT; JPO;	2003/10/05 17:50
		parallel) and (insulator or dielectric)) and CMP	DERWENT	

-	48	((((lower or bottom or first) adj electrode) same signal adj lines) same	USPAT; JPO;	2003/10/05 17:50
_	8745	parallel) and (insulator or dielectric) ((lower or bottom or first) adj electrode)	DERWENT USPAT;	2003/10/05 17:51
_	2	same lines (((lower or bottom or first) adj	JPO; DERWENT USPAT;	2003/10/05 17:52
	_	electrode) same lines) and "multi-layer" adj metallization	JPO; DERWENT	
_	5	"high-k" with MIM	USPAT; JPO; DERWENT	2003/10/05 17:54
_	2	("high-k" with MIM) and CMP	USPAT; JPO;	2003/10/05 18:11
-	2	VLSI with "multi-layer" adj metallization	DERWENT USPAT; JPO;	2003/10/05 18:11
_	4	VLSI same "multi-layer" adj metallization	DERWENT USPAT; JPO;	2003/10/05 18:12
_	2	"multi-layer" adj metallization and MIM	DERWENT USPAT; JPO;	2003/10/05 18:13
_	10	"MLM" and MIM	DERWENT USPAT; JPO;	2003/10/05 18:14
-	147	multi with metal and MIM	DERWENT USPAT; JPO;	2003/10/05 18:14
-	72	(multi with metal and MIM) and dielectric	DERWENT USPAT; JPO;	2003/10/05 18:14
_	67	((multi with metal and MIM) and dielectric) and electrode	DERWENT USPAT; JPO;	2003/10/05 18:14
_	11	(((multi with metal and MIM) and dielectric) and electrode) and CMP	DERWENT USPAT; JPO;	2003/10/05 18:18
_	102	MIM and VLSI	DERWENT USPAT; JPO;	2003/10/05 18:19
-	63	(MIM and VLSI) and dielectric	DERWENT USPAT; JPO;	2003/10/05 18:19
_	15	((MIM and VLSI) and dielectric) and CMP	DERWENT USPAT; JPO;	2003/10/05 18:19
-	13	(((MIM and VLSI) and dielectric) and CMP) and electrode	DERWENT USPAT; JPO;	2003/10/05 18:36
_	5	 ("5162258" "5812364" "5913126" "5918135" "5920775").PN.	DERWENT USPAT	2003/10/05 18:35
-	5	(("5162258" "5812364" "5913126" "5918135" "5920775").PN.) and MIM	USPAT; JPO;	2003/10/05 18:36
_	1	"5918135" "5920775").PN.) and MIM) and	DERWENT USPAT; JPO;	2003/10/05 18:38
-	0	"multi-layer" "multi-layer" with metallization and capacitro	DERWENT USPAT; JPO;	2003/10/05 18:38
_	126		DERWENT USPAT; JPO;	2003/10/05 18:38
_	94	("multi-layer" with metallization and capacitor) and dielectric	DERWENT USPAT; JPO;	2003/10/05 18:39
_	35	(("multi-layer" with metallization and capacitor) and dielectric) and electrode	DERWENT USPAT; JPO;	2003/10/05 18:39
		with etch\$	DERWENT	l

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-	2	((("multi-layer" with metallization and	USPAT;	2003/10/05 18:41
		capacitor) and dielectric) and electrode	JPO;	
1		with etch\$) and CMP	DERWENT	
-	0	(((("multi-layer" with metallization and	USPAT;	2003/10/05 18:41
		capacitor) and dielectric) and electrode	JPO;	
		with etch\$) and CMP) and dielectric adj	DERWENT	
		constant		
-	2	("6077742" "6184081").PN.	USPAT	2003/10/05 18:41
-	2	(("6077742" "6184081").PN.) and CMP	USPAT;	2003/10/05 18:42
			JPO;	
			DERWENT	
_	0	(("6077742" "6184081").PN.) and MIM	USPAT;	2003/10/05 18:48
			JPO;	
			DERWENT	
_	8	"6124199"	USPAT;	2003/10/05 18:53
			JPO;	
			DERWENT	•
-	99	(multi with level with metallization) and	USPAT;	2003/10/05 18:53
		capacitor	JPO;	
		•	DERWENT	
-	89	((multi with level with metallization) and	USPAT;	2003/10/05 18:53
		capacitor) and (insulator or dielectric)	JPO;	
		•	DERWENT	
-	81	(((multi with level with metallization)	USPAT;	2003/10/05 18:53
		and capacitor) and (insulator or	JPO;	
		dielectric)) and etch\$4	DERWENT	
-	4 4	((((multi with level with metallization)	USPAT;	2003/10/05 18:53
		and capacitor) and (insulator or	JPO;	
ł		dielectric)) and etch\$4) and electrode	DERWENT	
-	9	("5315141" "5323037" "5479316"	USPAT	2003/10/05 19:02
		"5686339" "5753558" "5792687"		
		"5926359" "6174770" "6376874").PN.		
-	8	("4335505" "4786612" "5068694"	USPAT	2003/10/05 19:17
	1	"5366920" "5436477" "5439840"	1	
		"5440174" "5670808").PN.		